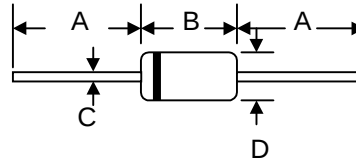


Features

- Fast Switching Speed
- Glass Package Version for High Reliability
- High Conductance
- Available in Both Through-Hole and Surface Mount Versions



1 N 4 1 4 8

Mechanical Data

- Case: DO-35, MiniMELF
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: DO-35 0.13 grams
MiniMELF 0.05 grams
- Marking: Cathode Band Only
- **Lead Free: For RoHS / Lead Free Version,**

DO-35		
Dim	Min	Max
A	25.40	—
B	—	4.00
C	—	0.60
D	—	2.00
All Dimensions in mm		

Maximum Ratings @T_A=25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V _{RM}	100	V
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	75	V
RMS Reverse Voltage	V _{R(RMS)}	53	V
Forward Continuous Current (Note 1)	I _{FM}	300	mA
Rectified Current (Average), Half Wave Rectification with Resistive Load and f ≥ 50MHz (Note 1)	I _O	150	mA
Non-Repetitive Peak Forward Surge Current @ t = 1.0s @ t = 1.0μs	I _{FSM}	1.0 2.0	A
Power Dissipation (Note 1) Derate Above 25°C	P _d	500 1.68	mW mW/°C
Thermal Resistance, Junction to Ambient Air (Note 1)	R _{θJA}	300	K/W
Operating and Storage Temperature Range	T _j , T _{STG}	-65 to +175	°C

Electrical Characteristics @T_A=25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
Maximum Forward Voltage	V _{FM}	—	1.0	V	I _F = 10mA
Maximum Peak Reverse Current	I _{RM}	—	5.0 50 30 25	μA μA μA nA	V _R = 75V V _R = 70V, T _j = 150°C V _R = 20V, T _j = 150°C V _R = 20V
Capacitance	C _j	—	4.0	pF	V _R = 0, f = 1.0MHz
Reverse Recovery Time	t _{rr}	—	4.0	ns	I _F = 10mA to I _R = 1.0mA V _R = 6.0V, R _L = 100Ω

Note: 1. Diode on Ceramic Substrate 10mm x 8mm x 0.7mm.

Typical Characteristics Curves

Fig.1- Power Derating Curve

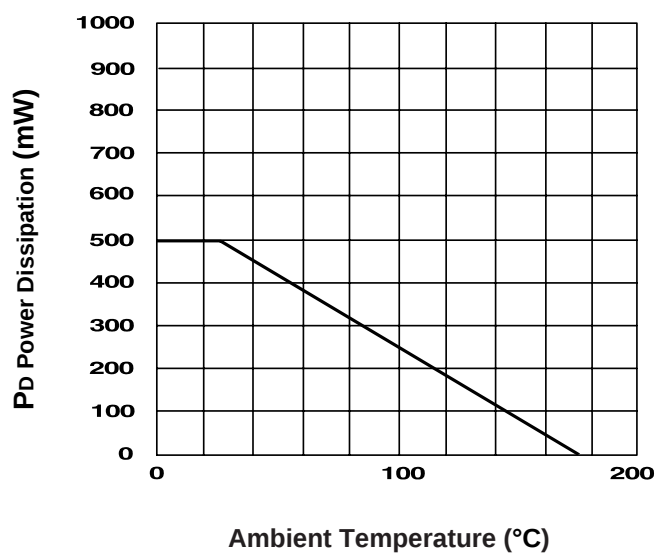


Fig.2- Typical Forward Characteristics

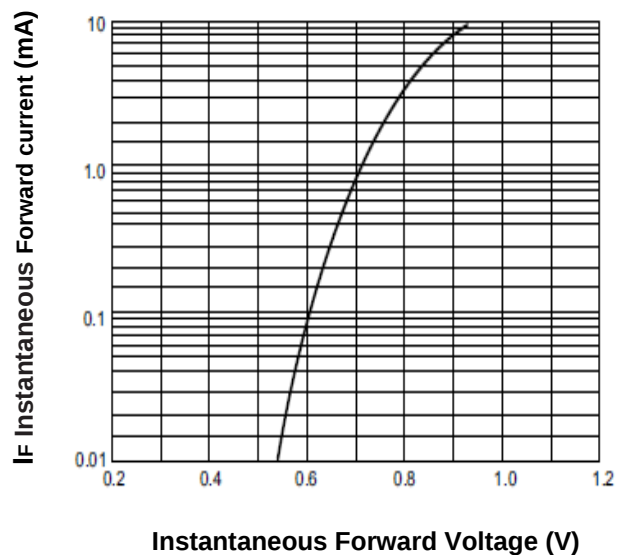


Fig.3- Typical junction capacitance

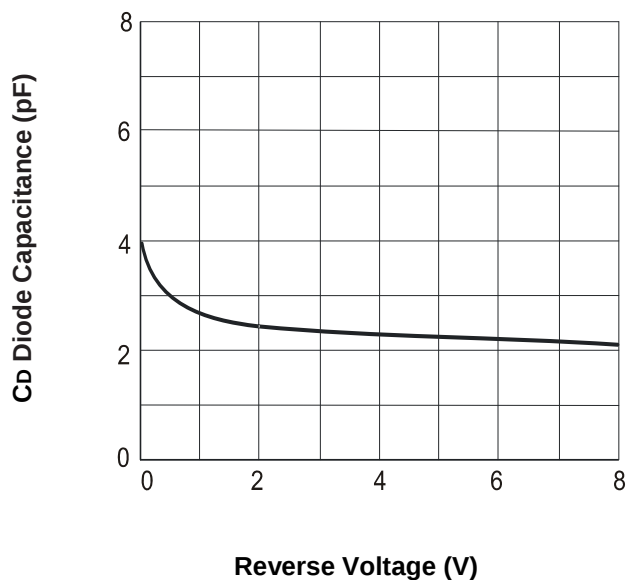


Fig.4- Typical Reverse Characteristics

